



PTO/SB/088 (08-03)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known	
		Application Number	10/634,220
		Filing Date	August 5, 2003
		First Named Inventor	Kryliouk et al.
		Art Unit	
		Examiner Name	
Sheet 1	of 1	Attorney Docket Number 5853-413	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
RL		NIKISHIN et al., "High quality GaN grown on Si(111) by gas source molecular beam epitaxy with ammonia," Applied Physics Letters, 75:2073-2075, 1999	
RL		ZHANG et al., "Enhanced optical emission from GaN films grown on a silicon substrate," Applied Physics Letters, 74:1984-1986, 1999	
RL		LINTHICUM et al., "PROCESS ROUTES FOR LOW DEFECT-DENSITY GAN ON VARIOUS SUBSTRATES EMPLOYING PENDEO-EPITAXIAL GROWTH TECHNIQUES," MRS Internet J. Nitride Semicond. Res. 4S1, G4.9, 1999	
RL		STRITTMATTER et al., "Low-pressure metal organic chemical vapor deposition of GaN on silicon(111) substrates using an AlAs nucleation layer," Applied Physics Letters, 74:1242-1244, 1999	
RL		SANCHEZ-GARCIA et al., "Ultraviolet electroluminescence in GaN/AlGaIn single-heterojunction light-emitting diodes grown on Si(111)," Journal of Applied Physics, 87:1569-1571, 2000	

Examiner Signature		Date Considered	6/18/04
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RL		KRYLIOUK et al., "SINGLE CRYSTAL GaN SUBSTRATE GROWN by HYDRIDE-METAL ORGANIC VAPOR PHASE EPITAXY (H-MOVPE)," Electromechanical Society Proceedings, 98-18:99-107, 1998.	
RL		LUKAS et al., "OPTIMIZATION OF PHASE DIAGRAMS BY A LEAST SQUARES METHOD USING SIMULTANEOUSLY DIFFERENT TYPES OF DATA," CALPHAD, 1:225-236, 1977.	
RL		SUNDMAN et al., "THE THERMO-CALC DATABANK SYSTEM," CALPHAD, 9:153-190, 1985.	

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